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FDN308P

P-Channel 2.5V Specified PowerTrench® MOSFET

General Description

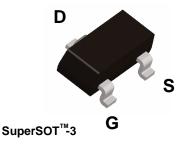
This P-Channel 2.5V specified MOSFET uses a rugged gate version of Fairchild's advanced PowerTrench process. It has been optimized for power management applications with a wide range of gate drive voltage (2.5V – 12V).

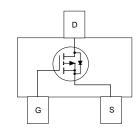
Applications

- · Power management
- Load switch
- · Battery protection

Features

- -20 V, -1.5 A. $R_{DS(ON)} = 125 \text{ m}\Omega$ @ $V_{GS} = -4.5 \text{ V}$ $R_{DS(ON)} = 190 \text{ m}\Omega$ @ $V_{GS} = -2.5 \text{ V}$
- · Fast switching speed
- High performance trench technology for extremely low Research.
- SuperSOT[™] -3 provides low R_{DS(ON)} and 30% higher power handling capability than SOT23 in the same footprint





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{DSS}	Drain-Source Voltage		-20	V
V _{GSS}	Gate-Source Voltage		±12	V
I _D	Drain Current - Continuous	(Note 1a)	-1.5	А
	- Pulsed		-10	
	Maximum Power Dissipation	(Note 1a)	0.5	W
P_D		(Note 1b)	0.46	
T _J , T _{STG}	Operating and Storage Junction Temperature Range		-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	250	°C/W
R _{θJC}	Thermal Resistance, Junction-to-Case	(Note 1)	75	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
308	FDN308P	7"	8mm	3000 units

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics			l	I	
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	-20			V
ΔBV _{DSS} ΔT _J	Breakdown Voltage Temperature Coefficient	$I_D = -250 \mu A$, Referenced to 25°C		-13		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μΑ
I _{GSSF}	Gate-Body Leakage, Forward	V _{GS} = 12 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage, Reverse	$V_{GS} = -12 \text{ V}$ $V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-0.6	-1.0	-1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250 \mu A$, Referenced to 25°C		3		mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	$V_{GS} = -4.5 \text{ V}, I_D = -1.5 \text{ A}$ $V_{GS} = -2.5 \text{ V}, I_D = -1.3 \text{ A}$ $V_{GS} = -4.5 \text{ V}, I_D = -1.5 \text{A} \text{ T}_J = 125 ^{\circ}\text{C}$		86 136 114	125 190 178	mΩ
I _{D(on)}	On-State Drain Current	$V_{GS} = -4.5 \text{ V}, \qquad V_{DS} = -5 \text{ V}$	-5			Α
g FS	Forward Transconductance	$V_{DS} = -5 \text{ V}, \qquad I_{D} = -1.5 \text{ A}$		12		S
Dynamic	: Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V},$		341		pF
Coss	Output Capacitance	f = 1.0 MHz		83		pF
C _{rss}	Reverse Transfer Capacitance	7		43		pF
t _{d(on)}	Turn-On Delay Time	$\begin{split} V_{DD} = -10 \ V, & I_D = -1 \ A, \\ V_{GS} = -4.5 \ V, & R_{GEN} = 6 \ \Omega \end{split}$		8	16	ns
t _r	Turn-On Rise Time			10	20	ns
t _{d(off)}	Turn-Off Delay Time			12	22	ns
t _f	Turn-Off Fall Time			8	16	ns
Qg	Total Gate Charge	$V_{DS} = -10V$, $I_D = -1.5 A$,		3.8	5.4	nC
Q_{gs}	Gate-Source Charge	$V_{GS} = -4.5 \text{ V}$		0.8		nC
Q_{gd}	Gate-Drain Charge			1.0		nC
Drain-S	ource Diode Characteristics	and Maximum Ratings				
Is	Maximum Continuous Drain-Source	<u> </u>			-0.42	Α
V_{SD}	Drain–Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = -0.42 \text{(Note 2)}$		-0.7	-1.2	V

Notes:

1. $R_{\theta,JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta,JC}$ is guaranteed by design while $R_{\theta,CA}$ is determined by the user's board design.



a) 250°C/W when mounted on a 0.02 in² pad of 2 oz. copper.

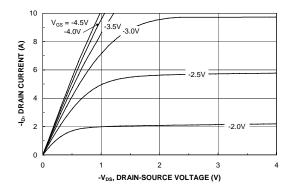


b) 270°C/W when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

Typical Characteristics



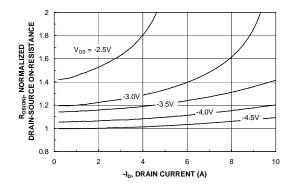
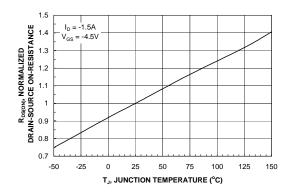


Figure 1. On-Region Characteristics.

Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.



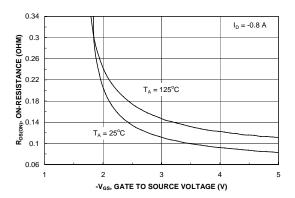
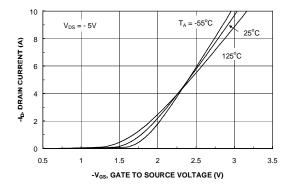


Figure 3. On-Resistance Variation withTemperature.

Figure 4. On-Resistance Variation with Gate-to-Source Voltage.



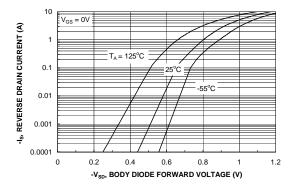
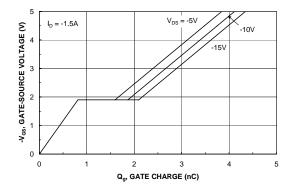


Figure 5. Transfer Characteristics.

Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics



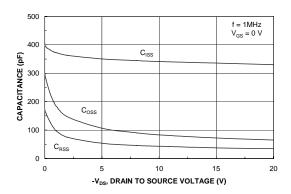
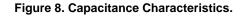
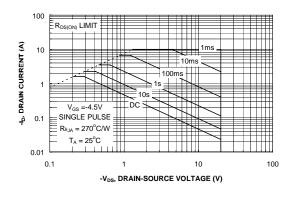


Figure 7. Gate Charge Characteristics.





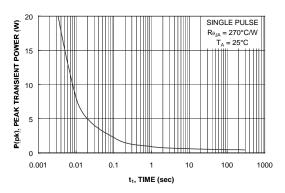


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

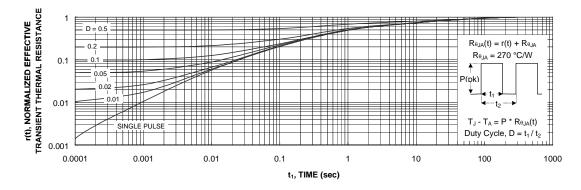


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b. Transient themal response will change depending on the circuit board design.

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